LDO Voltage Regulator -Adjustable Output, Load Dump Protection 60 V, 100 mA

LM2931, NCV2931 Series

The LM2931 series consists of positive fixed and adjustable output voltage regulators that are specifically designed to maintain proper regulation with an extremely low input-to-output voltage differential. These devices are capable of supplying output currents in excess of 100 mA and feature a low bias current of 0.4 mA at 10 mA output.

Designed primarily to survive in the harsh automotive environment, these devices will protect all external load circuitry from input fault conditions caused by reverse battery connection, two battery jump starts, and excessive line transients during load dump. This series also includes internal current limiting, thermal shutdown, and additionally, is able to withstand temporary power–up with mirror–image insertion.

Due to the low dropout voltage and bias current specifications, the LM2931 series is ideally suited for battery powered industrial and consumer equipment where an extension of useful battery life is desirable. The 'C' suffix adjustable output regulators feature an output inhibit pin which is extremely useful in microprocessor-based systems.

Features

- Input-to-Output Voltage Differential of < 0.6 V @ 100 mA
- Output Current in Excess of 100 mA
- Low Bias Current
- 60 V Load Dump Protection
- -50 V Reverse Transient Protection
- Internal Current Limiting with Thermal Shutdown
- Temporary Mirror-Image Protection
- Ideally Suited for Battery Powered Equipment
- Economical 5–Lead TO–220 Package with Two Optional Leadforms
- Available in Surface Mount SOP-8, D²PAK and DPAK Packages
- High Accuracy (±2.5%) Reference (LM2931AC) Available
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- Pb-Free Packages are Available

Applications

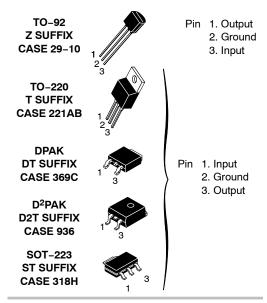
- Battery Powered Consumer Products
- Hand-held Instruments
- Camcorders and Cameras



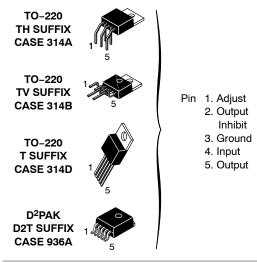
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FIXED OUTPUT VOLTAGE



ADJUSTABLE OUTPUT VOLTAGE

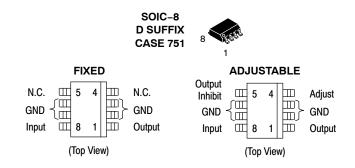


ORDERING INFORMATION

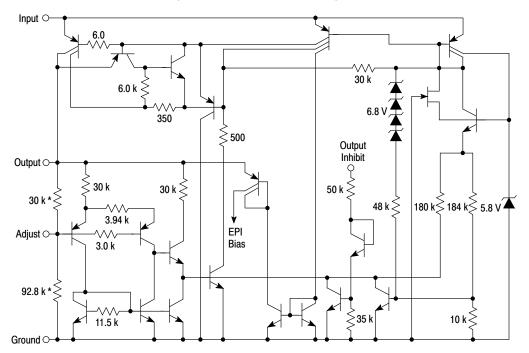
See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

DEVICE MARKING INFORMATION

See general marking and heatsink information in the device marking section on page 15 of this data sheet.







*Deleted on Adjustable Regulators

This device contains 26 active transistors.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage Continuous	VI	40	Vdc
Transient Input Voltage ($\tau \le 100 \text{ ms}$)	V _I (τ)	60	Vpk
Transient Reverse Polarity Input Voltage 1.0% Duty Cycle, $\tau \le 100$ ms	-V _I (τ)	-50	Vpk
Electrostatic Discharge Sensitivity (ESD) Human Body Model (HBM) Class 2, JESD22 A114–C Machine Model (MM) Class A, JESD22 A115–A Charged Device Model (CDM), JESD22 C101–C		2000 200 2000	V V V
Power Dissipation Case 29 (TO-92 Type) T _A = 25°C Thermal Resistance, Junction-to-Ambient	P _D R _{θJA}	Internally Limited 178	W °C/W
Thermal Resistance, Junction-to-Case Case 221A, 314A, 314B and 314D (TO-220 Type)	R _{0JC}	83	°C/W W
$T_A = 25^{\circ}C$ Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	Ρ _D R _{θJA} R _{θJC}	Internally Limited 65 5.0	°C/W °C/W
Case 318H (SOT-223) T _A = 25°C Thermal Resistance, Junction-to-Ambient	P _D R _{θJA}	Internally Limited 242	W °C/W
Thermal Resistance, Junction-to-Case Case 369A (DPAK) (Note 1) $T_A = 25^{\circ}C$	R _{0JC}	21 Internally Limited	°C/W W
Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	R _{θJA} R _{θJC}	92 6.0	°C/W °C/W
Case 751 (SOP-8) (Note 2) $T_A = 25^{\circ}C$ Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	P _D R _{θJA} R _{θJC}	Internally Limited 160 25	W °C/W °C/W
Case 936 and 936A (D ² PAK) (Note 3) T _A = 25°C Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case	P _D R _{0JA}	Internally Limited 70 5.0	W °C/W ∘C/W
Operating Ambient Temperature Range	R _{θJC} Τ _Α	5.0 - 40 to +125	°C/0°
Operating Die Junction Temperature	TJ	+150	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. DPAK Junction-to-Ambient Thermal Resistance is for vertical mounting. Refer to Figure 25 for board mounted Thermal Resistance.

2. SOP-8 Junction-to-Ambient Thermal Resistance is for minimum recommended pad size. Refer to Figure 24 for Thermal Resistance variation versus pad size.

3. D²PAK Junction-to-Ambient Thermal Resistance is for vertical mounting. Refer to Figure 26 for board mounted Thermal Resistance.

4. NCV rated devices are subjected to and meet the AECQ-100 quality standards.

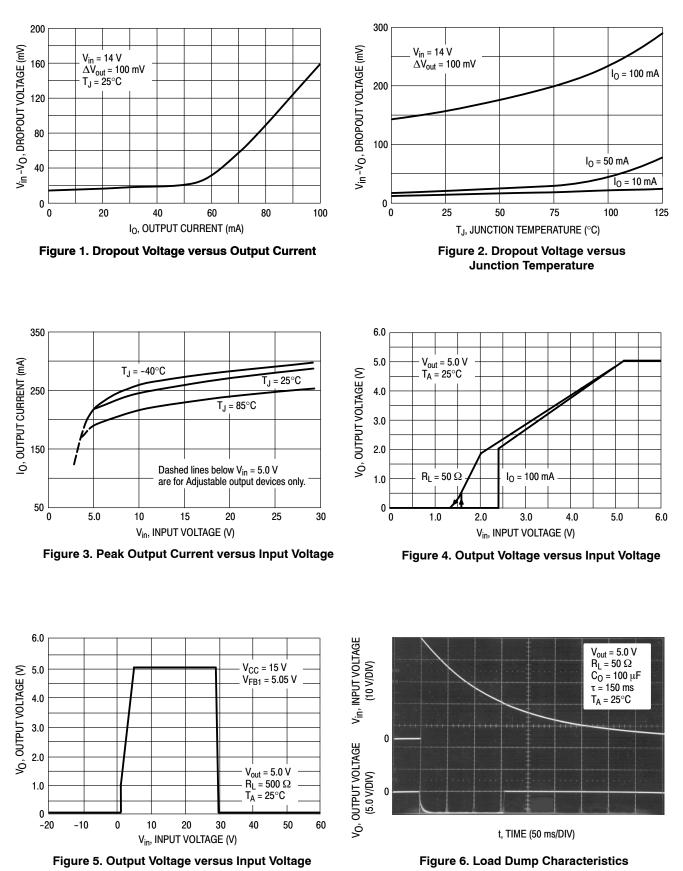
		LM2931	-5.0/NCV2	2931–5.0	LM2931A	-5.0/NCV2	931A-5.0	
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
FIXED OUTPUT	<u> </u>							
Output Voltage	Vo							V
V_{in} = 14 V, I_O = 10 mA, T_A = 25°C		4.75	5.0	5.25	4.81	5.0	5.19	
V_{in} = 6.0 V to 26 V, I_O \leq 100 mA, T_A = -40° to $+125^\circ C$		4.50	-	5.50	4.75	-	5.25	
Line Regulation	Reg _{line}							mV
V _{in} = 9.0 V to 16 V		-	2.0	10	-	2.0	10	
V _{in} = 6.0 V to 26 V		_	4.0	30	-	4.0	30	
Load Regulation (I _O = 5.0 mA to 100 mA)	Reg _{load}	-	14	50	-	14	50	mV
Output Impedance	ZO							mΩ
I_{O} = 10 mA, ΔI_{O} = 1.0 mA, f = 100 Hz to 10 kHz		-	200	-	_	200	-	
Bias Current	I _B							mA
V_{in} = 14 V, I _O = 100 mA, T _A = 25°C		-	5.8	30	-	5.8	30	
V_{in} = 6.0 V to 26 V, I_O = 10 mA, T_A = -40° to $+125^\circ C$		-	0.4	1.0	_	0.4	1.0	
Output Noise Voltage (f = 10 Hz to 100 kHz)	Vn	_	700	-	-	700	-	μVrms
Long Term Stability	S	_	20	-	-	20	-	mV/kHR
Ripple Rejection (f = 120 Hz)	RR	60	90	-	60	90	-	dB
Dropout Voltage	V _I –V _O							V
I _O = 10 mA		-	0.015	0.2	-	0.015	0.2	
I _O = 100 mA		-	0.16	0.6	-	0.16	0.6	
Over-Voltage Shutdown Threshold	V _{th(OV)}	26	29.5	40	26	29.5	40	V
Output Voltage with Reverse Polarity Input $(V_{in} = -15 \text{ V})$	-V _O	-0.3	0	-	-0.3	0	-	V

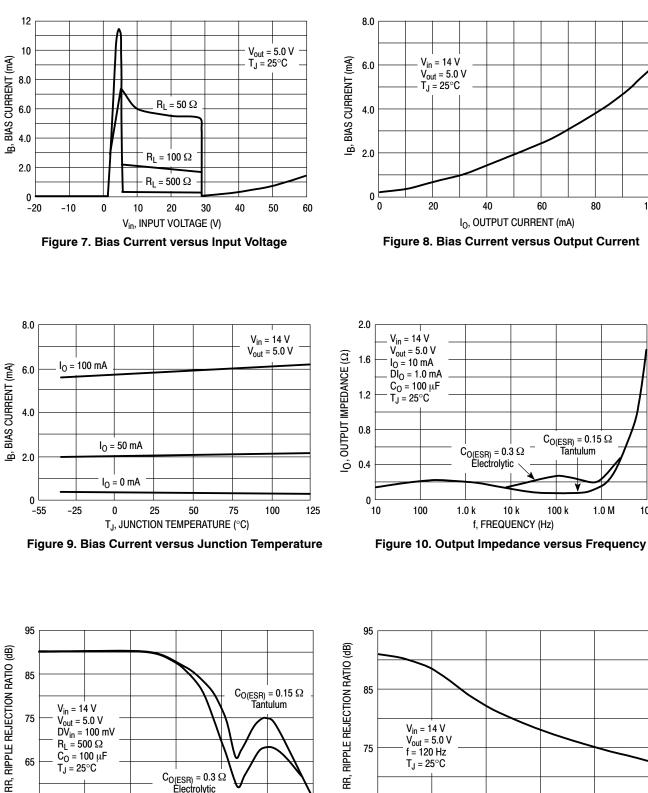
ELECTRICAL CHARACTERISTICS (V_{in} = 14 V, I_O = 10 mA, C_O = 100 μ F, C_{O(ESR)} = 0.3 Ω , T_A = 25°C [Note 5])

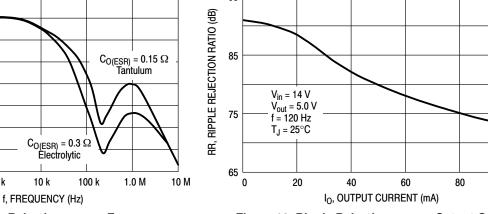
Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
 NCV devices are qualified for automotive use.

		LM29	31C/NCV	2931C	LM2931AC/NCV2931AC			
Characteristic	Symbol	Min	Тур	Max	Min	Тур	Max	Unit
ADJUSTABLE OUTPUT								
Reference Voltage (Note 8, Figure 18) $I_O = 10 \text{ mA}, T_A = 25^{\circ}\text{C}$ $I_O \le 100 \text{ mA}, T_A = -40 \text{ to } +125^{\circ}\text{C}$	V _{ref}	1.14 1.08	1.20 _	1.26 1.32	1.17 1.15	1.20 -	1.23 1.25	V
Output Voltage Range	V _{O range}	3.0 to 24	2.7 to 29.5	-	3.0 to 24	2.7 to 29.5	-	V
Line Regulation ($V_{in} = V_O + 0.6 V$ to 26 V)	Reg _{line}	-	0.2	1.5	-	0.2	1.5	mV/V
Load Regulation (I _O = 5.0 mA to 100 mA)	Reg _{load}	-	0.3	1.0	-	0.3	1.0	%/V
Output Impedance I_O = 10 mA, Δ I_O = 1.0 mA, f = 10 Hz to 10 kHz	Z _O	-	40	-	_	40	-	mΩ/V
Bias Current I _O = 100 mA I _O = 10 mA Output Inhibited (V _{th(OI)} = 2.5 V)	Ι _Β	- -	6.0 0.4 0.2	_ 1.0 1.0	- -	6.0 0.4 0.2	_ 1.0 1.0	mA
Adjustment Pin Current	I _{Adj}	-	0.2	-	-	0.2	-	μΑ
Output Noise Voltage (f = 10 Hz to 100 kHz)	V _n	-	140	-	-	140	-	μVrms/V
Long-Term Stability	S	-	0.4	-	-	0.4	-	%/kHR
Ripple Rejection (f = 120 Hz)	RR	0.10	0.003	-	0.10	0.003	-	%/V
Dropout Voltage $I_O = 10 \text{ mA}$ $I_O = 100 \text{ mA}$	V _I –V _O		0.015 0.16	0.2 0.6		0.015 0.16	0.2 0.6	V
Over-Voltage Shutdown Threshold	V _{th(OV)}	26	29.5	40	26	29.5	40	V
Output Voltage with Reverse Polarity Input $(V_{in} = -15 V)$	-V _O	-0.3	0	-	-0.3	0	-	V
$\begin{array}{llllllllllllllllllllllllllllllllllll$	V _{th(OI)}	- - 2.50 3.25	2.15 _ 2.26 _	1.90 1.20 - -	- - 2.50 3.25	2.15 _ 2.26 _	1.90 1.20 - -	V
Output Inhibit Threshold Current (V _{th(OI)} = 2.5 V)	I _{th(OI)}	_	30	50	-	30	50	μA

Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
 The reference voltage on the adjustable device is measured from the output to the adjust pin across R₁.









 $R_L = 500 \Omega$

C_O = 100 μF

100

1.0 k

T_J = 25°C

65

55

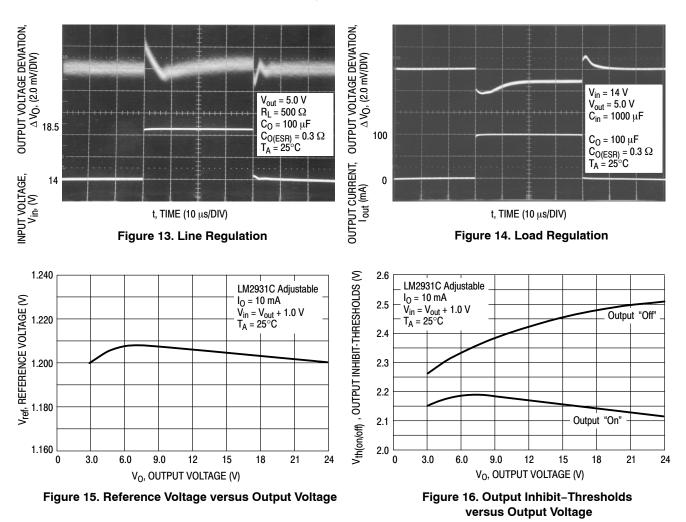
10



100

10 M

100



APPLICATIONS INFORMATION

The LM2931 series regulators are designed with many protection features making them essentially blow-out proof. These features include internal current limiting, thermal shutdown, overvoltage and reverse polarity input protection, and the capability to withstand temporary power-up with mirror-image insertion. Typical application circuits for the fixed and adjustable output device are shown in Figures 17 and 18.

The input bypass capacitor C_{in} is recommended if the regulator is located an appreciable distance ($\geq 4''$) from the supply input filter. This will reduce the circuit's sensitivity to the input line impedance at high frequencies.

This regulator series is not internally compensated and thus requires an external output capacitor for stability. The capacitance value required is dependent upon the load current, output voltage for the adjustable regulator, and the type of capacitor selected. The least stable condition is encountered at maximum load current and minimum output voltage. Figure 22 shows that for operation in the "Stable" region, under the conditions specified, the magnitude of the output capacitor impedance $|Z_0|$ must not exceed 0.4 Ω . This limit must be observed over the entire operating temperature range of the regulator circuit.

With economical electrolytic capacitors, cold temperature operation can pose a serious stability problem. As the electrolyte freezes, around -30° C, the capacitance will decrease and the equivalent series resistance (ESR) will increase drastically, causing the circuit to oscillate. Quality electrolytic capacitors with extended temperature ranges of -40° to $+85^{\circ}$ C and -55° to $+105^{\circ}$ C are readily available. Solid tantalum capacitors may be a better choice if small size is a requirement, however, the maximum $|Z_0|$ limit over temperature must be observed.

Note that in the stable region, the output noise voltage is linearly proportional to $|Z_O|$. In effect, C_O dictates the high frequency roll-off point of the circuit. Operation in the area titled "Marginally Stable" will cause the output of the regulator to exhibit random bursts of oscillation that decay in an under-damped fashion. Continuous oscillation occurs when operating in the area titled "Unstable". It is suggested that oven testing of the entire circuit be performed with maximum load, minimum input voltage, and minimum ambient temperature.

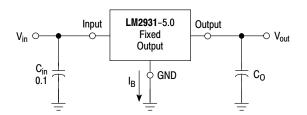
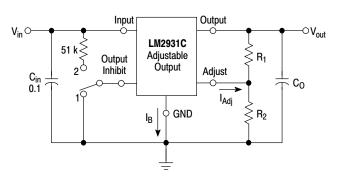


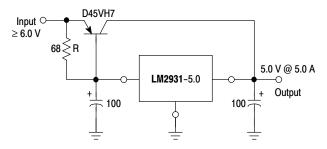
Figure 17. Fixed Output Regulator



Switch Position 1 = Output "On", 2 = Output "Off"

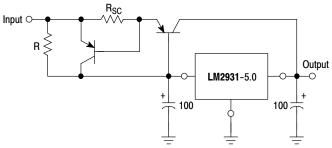
$$V_{out} = V_{ref} \left(1 + \frac{R_2}{R_1} \right) + I_{Adj} R_2$$
 22.5 k $\ge \frac{R_1 R_2}{R_1 + R_2}$

Figure 18. Adjustable Output Regulator



The LM2931 series can be current boosted with a PNP transistor. The D45VH7, on a heatsink, will provide an output current of 5.0 A with an input to output voltage differential of approximately 1.0 V. Resistor R in conjunction with the V_{BE} of the PNP determines when the pass transistor begins conducting. This circuit is not short circuit proof.

Figure 19. (5.0 A) Low Differential Voltage Regulator



The circuit of Figure 19 can be modified to provide supply protection against short circuits by adding the current sense resistor ${\sf R}_{SC}$ and an additional PNP transistor. The current sensing PNP must be capable of handling the short circuit current of the LM2931. Safe operating area of both transistors must be considered under worst case conditions.

Figure 20. Current Boost Regulator with Short Circuit Projection

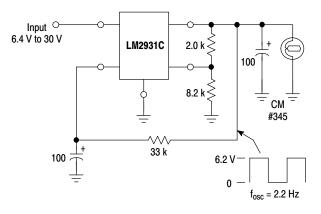
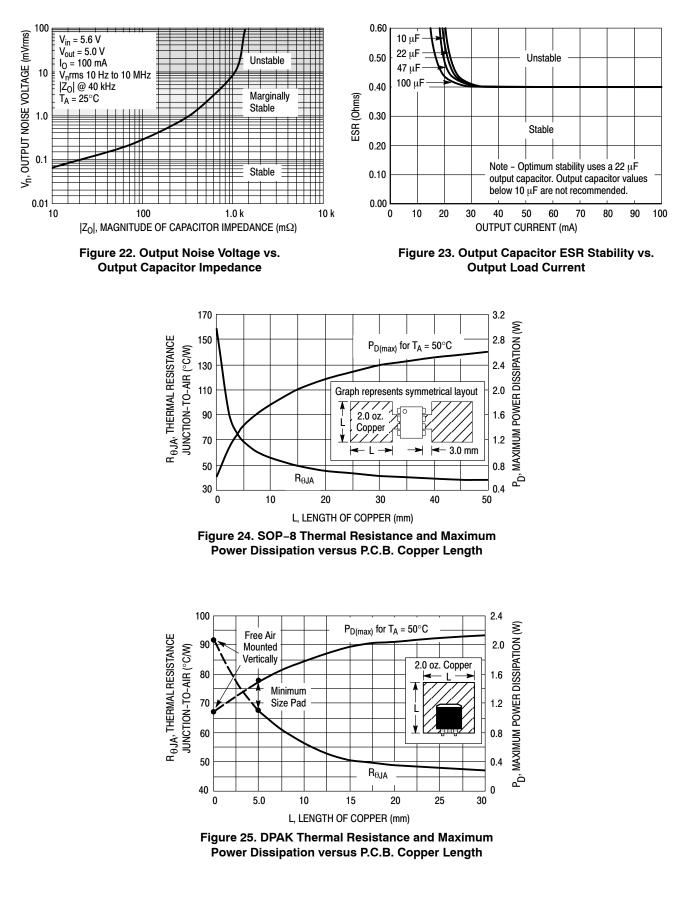


Figure 21. Constant Intensity Lamp Flasher



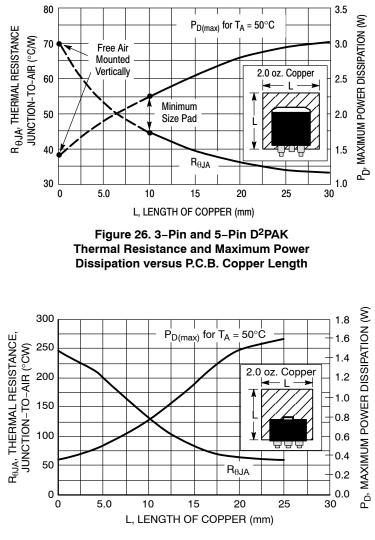


Figure 27. SOT-223 Thermal Resistance and Maximum Power Dissipation vs. P.C.B. Copper Length

DEFINITIONS

Dropout Voltage – The input/output voltage differential at which the regulator output no longer maintains regulation against further reductions in input voltage. Measured when the output decreases 100 mV from nominal value at 14 V input, dropout voltage is affected by junction temperature and load current.

Line Regulation – The change in output voltage for a change in the input voltage. The measurement is made under conditions of low dissipation or by using pulse techniques such that the average chip temperature is not significantly affected.

Load Regulation – The change in output voltage for a change in load current at constant chip temperature.

Maximum Power Dissipation – The maximum total device dissipation for which the regulator will operate within specifications.

Bias Current – That part of the input current that is not delivered to the load.

Output Noise Voltage – The rms AC voltage at the output, with constant load and no input ripple, measured over a specified frequency range.

Long–Term Stability – Output voltage stability under accelerated life test conditions with the maximum rated voltage listed in the devices electrical characteristics and maximum power dissipation.

ORDERING INFORMATION

	Ou	tput		
Device	Voltage	Tolerance	Package	Shipping [†]
LM2931AD-5.0	5.0 V	±3.8%	SOIC-8	98 Units / Rail
LM2931AD-5.0G	5.0 V	±3.8%	SOIC-8 (Pb-Free)	98 Units / Rail
LM2931AD-5.0R2	5.0 V	±3.8%	SOIC-8	2500 / Tape & Reel
LM2931AD-5.0R2G	5.0 V	±3.8%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2931ADT-5.0	5.0 V	±3.8%	DPAK	75 Units / Rail
LM2931ADT-5.0G	5.0 V	±3.8%	DPAK (Pb-Free)	75 Units / Rail
LM2931ADT-5.0RK	5.0 V	±3.8%	DPAK	2500 / VacPk Reel
LM2931ADT-5.0RKG	5.0 V	±3.8%	DPAK (Pb-Free)	2500 / VacPk Reel
LM2931AD2T-5.0	5.0 V	±3.8%	D ² PAK	50 Units / Rail
LM2931AD2T-5.0G	5.0 V	±3.8%	D ² PAK (Pb–Free)	50 Units / Rail
LM2931AD2T-5.0R4	5.0 V	±3.8%	D ² PAK	800 / VacPk Reel
LM2931AD2T-5R4G	5.0 V	±3.8%	D ² PAK (Pb–Free)	800 / VacPk Reel
LM2931AT-5.0	5.0 V	±3.8%	TO-220	50 Units / Rail
LM2931AT-5.0G	5.0 V	±3.8%	TO-220 (Pb-Free)	50 Units / Rail
LM2931AZ-5.0	5.0 V	±3.8%	TO-92	2000 / Inner Bag
LM2931AZ-5.0G	5.0 V	±3.8%	TO-92 (Pb-Free)	2000 / Inner Bag
LM2931AZ-5.0RA	5.0 V	±3.8%	TO-92	2000 / Tape & Reel
LM2931AZ-5.0RAG	5.0 V	±3.8%	TO-92 (Pb-Free)	2000 / Tape & Reel
LM2931AZ-5.0RP	5.0 V	±3.8%	TO-92	2000 / Ammo Pack
LM2931AZ-5.0RPG	5.0 V	±3.8%	TO-92 (Pb-Free)	2000 / Ammo Pack
LM2931D-5.0	5.0 V	$\pm 5.0\%$	SOIC-8	98 Units / Rail
LM2931D-5.0G	5.0 V	±5.0%	SOIC-8 (Pb-Free)	98 Units / Rail
LM2931D-5.0R2	5.0 V	$\pm 5.0\%$	SOIC-8	2500 / Tape & Reel
LM2931D-5.0R2G	5.0 V	±5.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2931D2T-5.0	5.0 V	±5.0%	D ² PAK	50 Units / Rail
LM2931D2T-5.0G	5.0 V	±5.0%	D ² PAK (Pb–Free)	50 Units / Rail
LM2931D2T-5.0R4	5.0 V	±5.0%	D ² PAK	800 / VacPk Reel
LM2931D2T-5.0R4G	5.0 V	±5.0%	D ² PAK (Pb–Free)	800 / VacPk Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 *NCV2931: T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

ORDERING INFORMATION

	Ou	tput		
Device	Voltage	Tolerance	Package	Shipping [†]
LM2931DT-5.0	5.0 V	±5.0%	DPAK	75 Units / Rail
LM2931DT-5.0G	5.0 V	±5.0%	DPAK (Pb-Free)	75 Units / Rail
LM2931T-5.0	5.0 V	±5.0%	TO-220	50 Units / Rail
LM2931T-5.0G	5.0 V	±5.0%	TO-220 (Pb-Free)	50 Units / Rail
LM2931Z-5.0	5.0 V	±5.0%	TO-92	2000 / Inner Bag
LM2931Z-5.0G	5.0 V	±5.0%	TO-92 (Pb-Free)	2000 / Inner Bag
LM2931Z-5.0RA	5.0 V	±5.0%	TO-92	2000 / Tape & Reel
LM2931Z-5.0RAG	5.0 V	±5.0%	TO-92 (Pb-Free)	2000 / Tape & Reel
LM2931Z-5.0RP	5.0 V	±5.0%	TO-92	2000 / Ammo Pack
LM2931Z-5.0RPG	5.0 V	±5.0%	TO–92 (Pb–Free)	2000 / Ammo Pack
LM2931CD	Adjustable	±5.0%	SOIC-8	98 Units / Rail
LM2931CDG	Adjustable	±5.0%	SOIC-8 (Pb-Free)	98 Units / Rail
LM2931CDR2	Adjustable	±5.0%	SOIC-8	2500 / Tape & Reel
LM2931CDR2G	Adjustable	±5.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2931CD2T	Adjustable	±5.0%	D ² PAK	50 Units / Rail
LM2931CD2TG	Adjustable	±5.0%	D ² PAK (Pb–Free)	50 Units / Rail
LM2931CD2TR4	Adjustable	±5.0%	D ² PAK	800 / VacPk Reel
LM2931CD2TR4G	Adjustable	±5.0%	D ² PAK (Pb–Free)	800 / VacPk Reel
LM2931CT	Adjustable	±5.0%	TO-220	50 Units / Rail
LM2931CTG	Adjustable	±5.0%	TO-220 (Pb-Free)	50 Units / Rail
LM2931ACD	Adjustable	±2.0%	SOIC-8	98 Units / Rail
LM2931ACDG	Adjustable	±2.0%	SOIC-8 (Pb-Free)	98 Units / Rail
LM2931ACDR2	Adjustable	±2.0%	SOIC-8	2500 / Tape & Reel
LM2931ACDR2G	Adjustable	±2.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LM2931ACD2TR4	Adjustable	±2.0%	D ² PAK	800 / VacPk Reel
LM2931ACD2TR4G	Adjustable	±2.0%	D ² PAK (Pb–Free)	800 / VacPk Reel
LM2931ACTV	Adjustable	±2.0%	TO-220	50 Units / Rail
LM2931ACTVG	Adjustable	±2.0%	TO-220 (Pb-Free)	50 Units / Rail

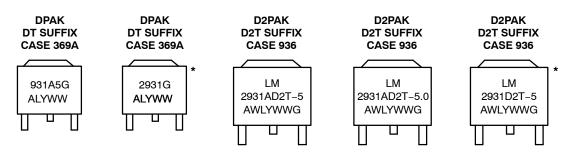
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 *NCV2931: T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

ORDERING INFORMATION

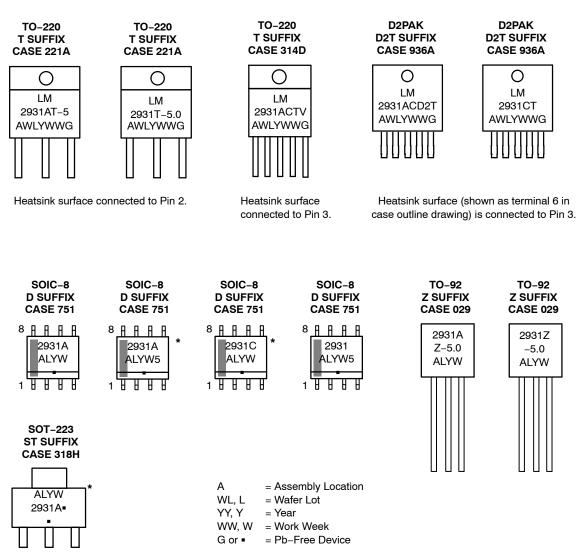
	Out	tput		
Device	Voltage	Tolerance	Package	Shipping [†]
NCV2931ACDR2*	Adjustable	±2.5%	SOIC-8	2500 / Tape & Reel
NCV2931ACDR2G*	Adjustable	±2.5%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2931AD-5.0R2*	5.0 V	±3.8%	SOIC-8	2500 / Tape & Reel
NCV2931AD-5.0R2G*	5.0 V	±3.8%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2931AST-5.0T3*	5.0 V	±3.8%	SOT-223	4000 / Tape & Reel
NCV2931AST-5.0T3G*	5.0 V	±3.8%	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV2931AZ-5.0G*	5.0 V	±3.8%	TO–92 (Pb–Free)	2000 / Inner Bag
NCV2931AZ-5.0RAG*	5.0 V	±3.8%	TO-92 (Pb-Free)	2000 / Tape & Reel
NCV2931CDR2*	Adjustable	±5.0%	SOIC-8	2500 / Tape & Reel
NCV2931CDR2G*	Adjustable	±5.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2931D-5.0R2*	5.0 V	±5.0%	SOIC-8	2500 / Tape & Reel
NCV2931D-5.0R2G*	5.0 V	±5.0%	SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV2931ADT-5.0RK*	5.0 V	±3.8%	DPAK	2500 / Tape & Reel
NCV2931ADT5.0RKG*	5.0 V	±3.8%	DPAK (Pb-Free)	2500 / Tape & Reel
NCV2931DT-5.0RK*	5.0 V	±5.0%	DPAK	2500 / Tape & Reel
NCV2931DT-5.0RKG*	5.0 V	±5.0%	DPAK (Pb–Free)	2500 / Tape & Reel
NCV2931ACD2TR4G*	Adjustable	±2.5%	D ² PAK (Pb–Free)	800 / VacPk Reel
NCV2931D2T-5.0R4*	5.0 V	±5.0%	D ² PAK	800 / VacPk Reel
NCV2931D2T5.0R4G*	5.0 V	±5.0%	D ² PAK (Pb-Free)	800 / VacPk Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 *NCV2931: T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MARKING DIAGRAMS



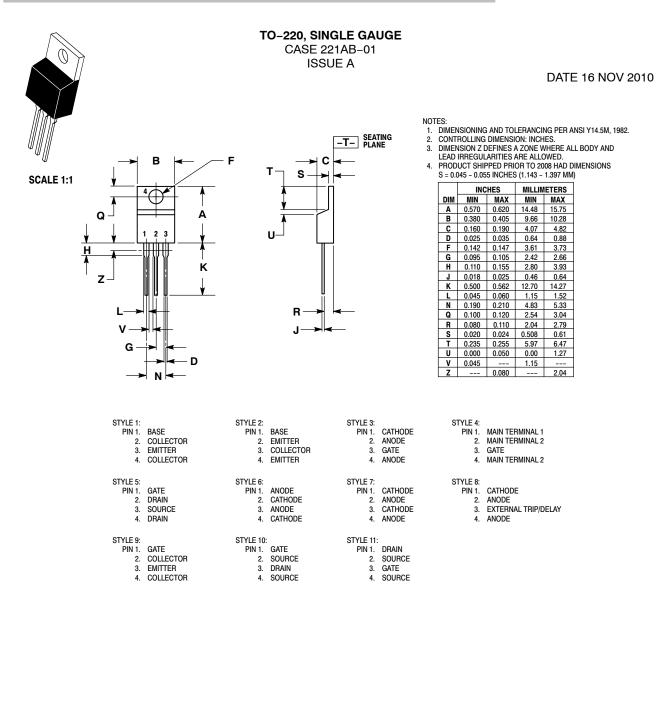
Heatsink surface (shown as terminal 4 in case outline drawing) is connected to Pin 2.



*This marking diagram also applies to NCV2931.

1 2 3

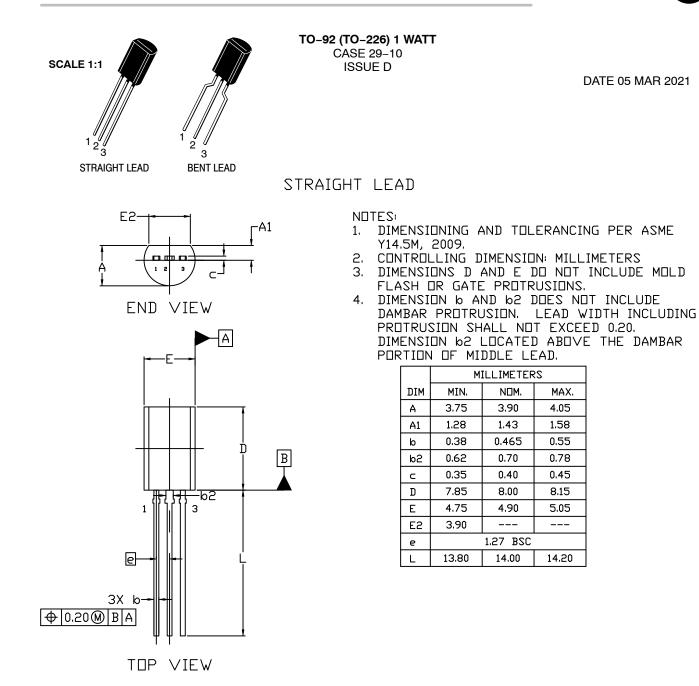




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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS





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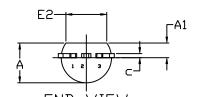
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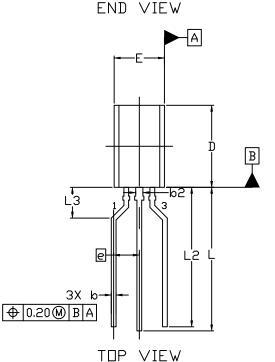


TO-92 (TO-226) 1 WATT CASE 29–10 ISSUE D

DATE 05 MAR 2021

FORMED LEAD





NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS,
- 4. DIMENSION ७ AND ७2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION ७2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	M	ILLIMETER	22
DIM	MIN.	NDM.	MAX.
Α	3.75	3.90	4.05
A1	1.28	1.43	1.58
σ	0.38	0.465	0.55
b2	0.62	0.70	0.78
с	0.35	0.40	0.45
D	7.85	8.00	8.15
Е	4.75	4.90	5.05
E2	3.90		
e	2.50 BSC		
L	13.80	14.00	14.20
L2	13.20	13.60	14.00
L3		3.00 REF	

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TO-92 (TO-226) 1 WATT CASE 29-10 ISSUE D

DATE 05 MAR 2021

2. SOURCE

STYLE 5: PIN 1. DRAIN

2.	EMITTER BASE COLLECTOR
STYLE 6: PIN 1. 2. 3.	SOURCE & SUBSTRATE
2.	ANODE CATHODE & ANODE CATHODE
2.	ANODE GATE CATHODE
2.	COLLECTOR EMITTER BASE
	V _{CC} GROUND 2 OUTPUT
	GATE DRAIN SOURCE

STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2 STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT STYLE 32 PIN 1. BASE 2. COLLECTOR 3. EMITTER

style Pin	1. 2.	ANODE ANODE CATHODE
STYLE PIN	1. 2.	DRAIN GATE SOURCE & SUBSTRATE
STYLE PIN	1. 2.	ANODE 1 GATE CATHODE 2
STYLE PIN	1. 2.	ANODE CATHODE NOT CONNECTED
STYLE PIN	1. 2.	GATE SOURCE DRAIN
Style Pin	1. 2.	CATHODE ANODE GATE
STYLE PIN	1. 2.	RETURN INPUT OUTPUT

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2 STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE

STYLE 34:

PIN 1. INPUT

2. GROUND 3. LOGIC

3. GATE STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2 STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE STYLE 35: PIN 1. GATE 2. COLLECTOR

3. EMITTER

GENERIC MARKING DIAGRAM*

XXXXX XXXXX ALYW

XXXX = Specific Device Code

- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
 - = Pb-Free Package

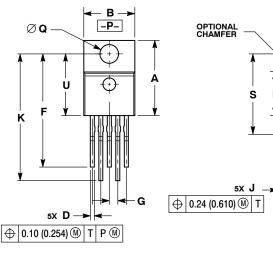
(Note: Microdot may be in either location)

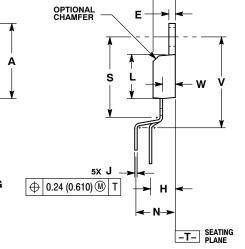
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DATE 01/07/1994

SCALE 1:1





TO-220 5 LEAD OFFSET CASE 314B-05

ISSUE L

С

NOTES:

IDIRESIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION D DOES NOT INCLUDE INTERCONNECT BAR (DAMBAR) PROTRUSION. DIMENSION D INCLUDING PROTRUSION SHALL NOT EXCEED 0.043 (1.092) MAXIMUM.

	INC	HES	MILLIMETER	
DIM	MIN	MAX	MIN	MAX
Α	0.572	0.613	14.529	15.570
В	0.390	0.415	9.906	10.541
c	0.170	0.180	4.318	4.572
D	0.025	0.038	0.635	0.965
н	0.048	0.055	1.219	1.397
F	0.850	0.935	21.590	23.749
G	0.067	BSC	1.702 BSC	
Н	0.166	BSC	4.216 BSC	
J	0.015	0.025	0.381	0.635
Κ	0.900	1.100	22.860	27.940
L	0.320	0.365	8.128	9.271
Ν	0.320	BSC	8.128 BSC	
Ø	0.140	0.153	3.556	3.886
s	0.620			15.748
U	0.468	0.505	11.888	12.827
۷		0.735		18.669
W	0.090	0.110	2.286	2.794

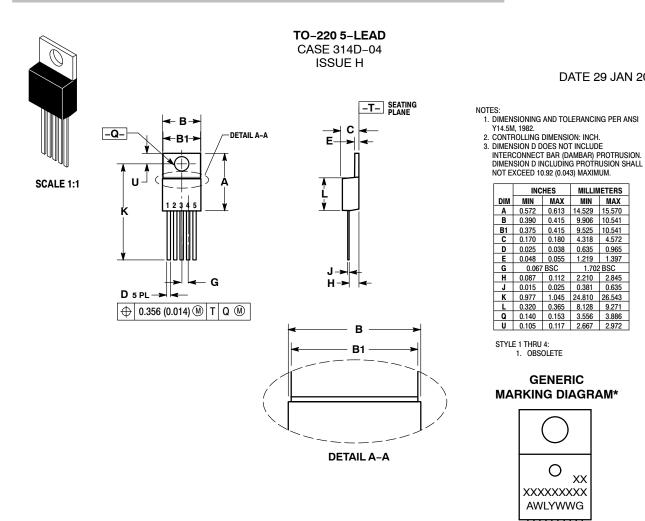
STYLE 1 THRU 4: CANCELLED



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DATE 29 JAN 2010

MILLIMETERS

 2.210
 2.845

 0.381
 0.635

XX

= Assembly Location

WL = Wafer Lot

= Year WW = Work Week G = Pb-Free Package *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " .",

may or may not be present.

Α

Υ

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SOT-223 CASE 318H ISSUE B DATE 13 MAY 2020 A NDTES SCALE 2:1 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009. CONTROLLING DIMENSION: MILLIMETERS DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS DG GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE. LEAD DIMENSIONS & AND &1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBBAR PROTRUSION IS 0.08mm PER SIDE. DATUMS A AND B ARE DETERMINED AT DATUM H. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS & AND &1. DIMENSIONING AND TOLERANCING PER ASME 1. b1 2 з. В 4. 5. 6. 7. b AND b1. MILLIMETERS DIM MIN. NITM. MAX. e ___ ___ 1.80 k Α \oplus 0.10 \otimes C A B 0.02 0.06 0.11 A1 TOP VIEW NDTE 7 0.60 0.74 0.88 b 2.90 3.10 b1 3.00 DETAIL A 0.24 ____ 0.35 С H 6.70 D 6.30 6.50 Е 6.70 7.00 7.30 E1 3.30 3.50 3.70 0.10 C 2.30 BSC e SIDE VIEW FND VIEW L 0.25 ___ i 10° 0° ____ -3.80 2.00 Α1 DETAIL A 8.30 3x= Assembly Location GENERIC A 2.00 **MARKING DIAGRAM*** Y = Year = Work Week w XXXXX = Specific Device Code = Pb-Free Package 5'30 AYW 3x 1.50 (Note: Microdot may be in either location) XXXXX= PITCH *This information is generic. Please refer to RECOMMENDED MOUNTING FOOTPRINT device data sheet for actual part marking. For additional information on our Pb-Free strategy Pb-Free indicator, "G" or microdot "•", may ж and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D. or may not be present. Some products may not follow the Generic Marking. Electronic versions are uncontrolled except when accessed directly from the Document Repository. **DOCUMENT NUMBER:** 98ASH70634A Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DESCRIPTION:** SOT-223 PAGE 1 OF 1

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR З. 4. EMITTER EMITTER 5. 6. BASE 7 BASE 8. EMITTER STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. 5. GATE 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6. BASE, DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. 4. TXE 5. RXE 6. VFF GND 7. 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 З. CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C З. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. EMITTER, #1 BASE, #2 2. З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 З. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: PIN 1. GROUND BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND BIAS 2 INPUT 6. 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. 5. P-DRAIN 6. P-DRAIN N-DRAIN 7. 8. N-DRAIN STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC I/O LINE 3 4. 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt ENABLE З. 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: PIN 1. DRAIN 1 DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1
STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd
STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 7. DRAIN 1 8. DRAIN 1
STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON
STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1
STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT
STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN

DATE 16 FEB 2011

STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE, #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER З. COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE CATHODE COLLECTOR/ANODE 6. 7. COLLECTOR/ANODE 8. STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET 3. 4. GND 5. 6. V MON VBULK 7. VBULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

7.

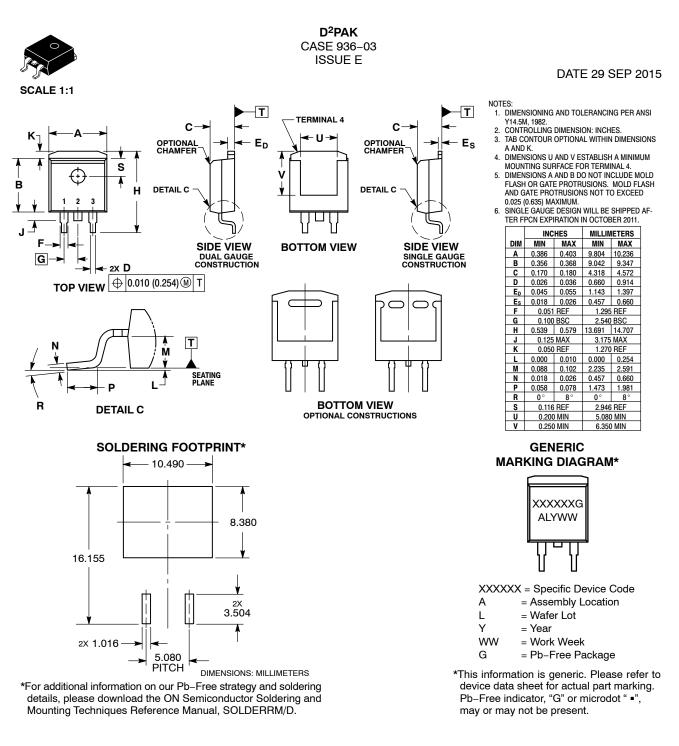
8

rights of others.

COLLECTOR, #1

COLLECTOR, #1





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 D²PAK
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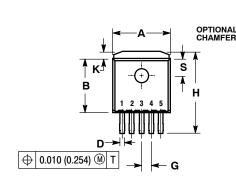


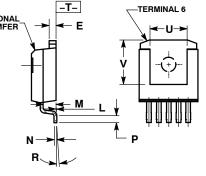


D²PAK 5-LEAD CASE 936A-02 **ISSUE D**

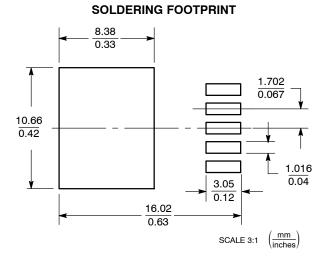
DATE 15 SEP 2015

SCALE 1:1





¥ С 88088

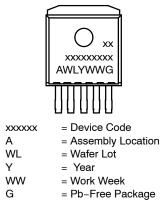


NOTES:

- NUTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. TAB CONTOUR OPTIONAL WITHIN DIMENSIONS A AND K
- 4.
- AND K. DIMENSIONS U AND V ESTABLISH A MINIMUM MOUNTING SURFACE FOR TERMINAL 6. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.025 5. (0.635) MAXIMUM.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.386	0.403	9.804	10.236	
В	0.356	0.368	9.042	9.347	
С	0.170	0.180	4.318	4.572	
D	0.026	0.036	0.660	0.914	
Е	0.045	0.055	1.143	1.397	
G	0.067 BSC		1.702 BSC		
Н	0.539	0.579	13.691	14.707	
К	0.050	REF	1.270 REF		
L	0.000	0.010	0.000	0.254	
М	0.088	0.102	2.235	2.591	
Ν	0.018	0.026	0.457	0.660	
Р	0.058	0.078	1.473	1.981	
R	0 °	8°	0 °	8°	
S	0.116 REF		2.946 REF		
U	0.200 MIN		5.080 MIN		
v	0.250 MIN		6.350 MIN		

GENERIC **MARKING DIAGRAM***



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

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